



DSR-14725

October 24, 2003

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/627,796 07/25/03

Taner Dosluoglu

TUNNELING FLOATING GATE APS PIXEL

Grp. Art Unit: _____

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

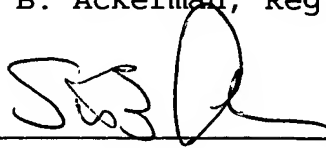
The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on October 27, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 10/27/03

DSR-14725

U.S. Patent 6,008,486 to Stam et al., "Wide Dynamic Range Optical Sensor," describes a method for increasing effective integration time of an optical sensor.

U.S. Patent 6,501,109 to Chi, "Active CMOS Pixel With Exponential Output Based on the GIDL Mechanism," describes an active pixel sensor cell formed in a semiconductor substrate utilizing a polysilicon floating gate.

U.S. Patent 5,936,866 to Seitz et al., "Light-Detection System with Programmable Offset Current," describes a photo-electric semiconductor light-detection device with programmable dynamic performance.

U.S. Patent 6,350,979 to Jing, "CMOS Image Sensor with High Quantum Efficiency," describes a CMOS image sensor having a floating gate with a comb structure.

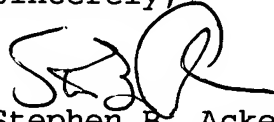
U.S. Patent 6,166,768 to Fossum et al., "Active Pixel Sensor Array with Simple Floating Gate Pixels," describes an active pixel sensor array, formed using CMOS integrated circuits, using floating gate pixels.

DSR-14725

U.S. Patent 5,608,243 to Chi et al., "Single Split-Gate MOS Transistor Active Pixel Sensor Cell with Automatic Anti-Blooming and Wide Dynamic Range," describes a split-gate MOS transistor active pixel sensor cell which utilizes a split gate.

U.S. Patent 5,541,402 to Ackland et al., "Imaging Active Pixel Device Having a Non-Destructive Read-Out Gate," describes an imaging pixel which has a floating gate pixel node capable of nondestructive readout and source follower output circuitry.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a large, stylized flourish extending from the end.

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

Document Number (Sequence)

DSR-14725

Application Number

10/627,796

**01 INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**

OCT 29 2003 (Use several sheets if necessary)

Applicant

Taner Dosluoglu

Filing Date

07/25/03

Drawn Art Unit

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE IF APPROPRIATE
6008486	12/28/99	Stam et al.	250	208.1	12/31/97
6501109	12/31/02	Chi	257	223	8/29/01
5936866	8/10/99	Seitz et al.	364	490	9/3/96
6350979	2/26/02	Jing	250	208.1	4/28/99
6166768	12/26/00	Fossum et al.	348	308	1/22/97
5608243	3/4/97	Chi et al.	257	249	10/19/95
5541402	7/30/96	Ackland et al.	250	208.1	10/17/94

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portlark Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant